

8-Bit Register

Features

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 5.8 ns max. (Com'l)
- FCT-A speed at 7.2 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times
- ESD > 2000V
- Fully compatible with TTL input and output logic levels

- Sink current 64 mA (Com'l), 32 mA (Mil)
- Source current 32 mA (Com'l), 12 mA (Mil)
- Buffered common clock
- Buffered, asynchronous master reset
- Edge-triggered D flip-flops
- CMOS for low-power consumption, typically one-third of FAST Bipolar Logic

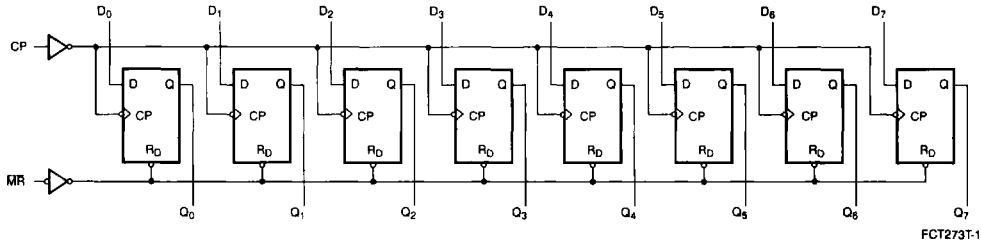
Functional Description

The FCT273T consists of eight edge-triggered D-type flip-flops with

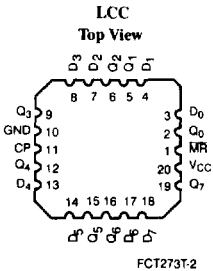
individual D inputs and Q outputs. The common buffered clock (CP) and master reset (MR) load and reset all flip-flops simultaneously. The FCT273T is an edge-triggered register. The state of each D input (one set-up time before the LOW-to-HIGH clock transition) is transferred to the corresponding flip-flop's Q output. All outputs will be forced LOW by a low voltage level on the MR input.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

Logic Block Diagram

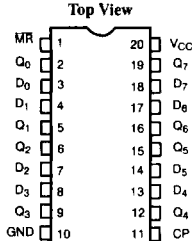


Pin Configurations



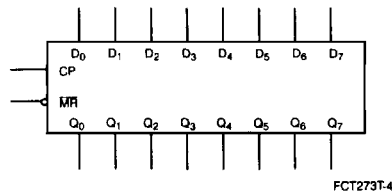
FCT273T-2

DIP/SOIC/QSOP



FCT273T-3

Logic Symbol



FCT273T-4

Function Table⁽¹⁾

Operating Mode	Inputs			Output
	\overline{MR}	CP	D	Q
Reset (clear)	L	X	X	L
Load '1'	H	\uparrow	h	H
Load '0'	H	\uparrow	l	L

Note:

1. H = HIGH Voltage Level steady state
h = HIGH Voltage Level one set-up time prior to LOW-to-HIGH clock transition
L = LOW Voltage Level steady state
l = LOW Voltage Level one set-up time prior to the LOW-to-HIGH transition
X = Don't Care
 \uparrow = LOW-to-HIGH clock transition



Maximum Ratings^[2, 3]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C
 Ambient Temperature with Power Applied -65°C to +135°C
 Supply Voltage to Ground Potential -0.5V to +7.0V
 DC Input Voltage -0.5V to +7.0V
 DC Output Voltage -0.5V to +7.0V
 DC Output Current (Maximum Sink Current/Pin) 120 mA
 Power Dissipation 0.5W

Static Discharge Voltage >2001V (per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V _{CC}
Commercial	CT	0°C to +70°C	5V ± 5%
Commercial	T, AT	-40°C to +85°C	5V ± 5%
Military ^[4]	All	-55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ^[5]	Max.	Unit	
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =-32 mA	Com'l	2.0		V	
		V _{CC} =Min., I _{OH} =-15 mA	Com'l	2.4	3.3	V	
		V _{CC} =Min., I _{OH} =-12 mA	Mil	2.4	3.3	V	
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =64 mA	Com'l		0.3	0.55	V
		V _{CC} =Min., I _{OL} =32mA	Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage		2.0			V	
V _{IL}	Input LOW Voltage				0.8	V	
V _H	Hysteresis ^[6]	All inputs		0.2		V	
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =-18 mA		-0.7	-1.2	V	
I _I	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}			5	μA	
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V			±1	μA	
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V			±1	μA	
I _{OS}	Output Short Circuit Current ^[7]	V _{CC} =Max., V _{OUT} =0.0V	-60	-120	-225	mA	
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V			±1	μA	

Capacitance^[6]

Parameter	Description	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Notes:

- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- T_A is the "instant on" case temperature.
- Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} =Max., V _{IN} ≤0.2V, V _{IN} ≥V _{CC} -0.2V	0.1	0.2	mA
ΔI _{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	V _{CC} =Max., V _{IN} =3.4V ^[8] f ₁ =0, Outputs Open	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[9]	V _{CC} =Max., One Bit Toggling, 50% Duty Cycle, Outputs Open, MR=V _{CC} , V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	0.06	0.12	mA/ MHz
I _C	Total Power Supply Current ^[10]	V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =5 MHz, MR=V _{CC} , V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	0.7	1.4	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =5 MHz, MR=V _{CC} , V _{IN} =3.4V or V _{IN} =GND	1.2	3.4	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f ₁ =2.5 MHz, MR=V _{CC} , V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	1.6	3.2 ^[11]	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f ₁ =2.5 MHz, MR=V _{CC} , V _{IN} =3.4V or V _{IN} =GND	3.9	12.2 ^[11]	mA

Notes:

8. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.
9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
10. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
 I_C = I_{CC} + ΔI_{CC}D_HN_T + I_{CCD}(f₀/2 + f₁N₁)
 I_{CC} = Quiescent Current with CMOS input levels
 ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
 D_H = Duty Cycle for TTL inputs HIGH

- N_T = Number of TTL inputs at D_H
 - I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)
 - f₀ = Clock frequency for registered devices, otherwise zero
 - f₁ = Input signal frequency
 - N₁ = Number of inputs changing at f₁
- All currents are in milliamps and all frequencies are in megahertz.
11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Switching Characteristics Over the Operating Range

Parameter	Description	FCT273T				FCT273AT				Unit	Fig. No. ^[13]
		Military		Commercial		Military		Commercial			
		Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.		
t _{PLH} t _{PHL}	Propagation Delay Clock to Output	2.0	15.0	2.0	13.0	2.0	8.3	2.0	7.2	ns	1, 5
t _{PLH} t _{PHL}	Propagation Delay MR to Output	2.0	15.0	2.0	13.0	2.0	8.3	2.0	7.2	ns	1, 6
t _s	Set-Up Time HIGH or LOW D to Clock	3.5		2.0		2.0		2.0		ns	4
t _H	Hold Time HIGH or LOW D to Clock	2.0		1.5		1.5		1.5		ns	4
t _w	Clock Pulse Width HIGH or LOW	7.0		6.0		6.0		6.0		ns	5
t _w	MR Pulse Width LOW	7.0		6.0		6.0		6.0		ns	6
t _{REC}	Recovery Time MR to Clock	5.0		2.0		2.5		2.0		ns	6

Parameter	Description	FCT273CT				Unit	Fig. No. ^[13]
		Military		Commercial			
		Min. ^[12]	Max.	Min. ^[12]	Max.		
t _{PLH} t _{PHL}	Propagation Delay Clock to Output	2.0	6.5	2.0	5.8	ns	1, 5
t _{PLH} t _{PHL}	Propagation Delay MR to Output	2.0	6.8	2.0	6.1	ns	1, 6
t _s	Set-Up Time HIGH or LOW D to Clock	2.0		2.0		ns	4
t _H	Hold Time HIGH or LOW D to Clock	1.5		1.5		ns	4
t _w	Clock Pulse Width HIGH or LOW	6.0		6.0		ns	5
t _w	MR Pulse Width LOW	6.0		6.0		ns	6
t _{REC}	Recovery Time MR to Clock	2.5		2.0		ns	6

Notes:

12. Minimum limits are guaranteed but not tested on Propagation Delays. 13. See "Parameter Measurement Information" in the General Information Section.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
5.8	CY74FCT273CTPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT273CTQC	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT273CTSOC	S5	20-Lead (300-Mil) Molded SOIC	
6.5	CY54FCT273CTDMB	D6	20-Lead (300-Mil) CerDIP	Military
	CY54FCT273CTLMB	L61	20-Square Leadless Chip Carrier	
7.2	CY74FCT273ATPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT273ATQC	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT273ATSOC	S5	20-Lead (300-Mil) Molded SOIC	
8.3	CY54FCT273ATDMB	D6	20-Lead (300-Mil) CerDIP	Military
	CY54FCT273ATLMB	L61	20-Square Leadless Chip Carrier	
13.0	CY74FCT273TPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT273TQC	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT273TSOC	S5	20-Lead (300-Mil) Molded SOIC	
15.0	CY54FCT273TDMB	D6	20-Lead (300-Mil) CerDIP	Military
	CY54FCT273TLMB	L61	20-Square Leadless Chip Carrier	

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